

**Vishay Siliconix** 

## N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	<b>R<sub>DS(on)</sub> (</b> Ω)	I <sub>D</sub> (A)		
100	0.250 at V <sub>GS</sub> = 10 V	1.5		

#### **FEATURES**

- Halogen-free According to IEC 61249-2-21 ٠ Definition
- 100 % R<sub>g</sub> and UIS Tested
  TrenchFET<sup>®</sup> Power MOSFET
- Compliant to RoHS Directive 2002/95/EC •



Available

**TO-236** (SOT-23) G 1 D 3 s 2 Top View Si2328DS (D8)\* \*Marking Code

Ordering Information: Si2328DS-T1-E3 (Lead (Pb)-free) Si2328DS-T1-GE3 (Lead (Pb)-free and Halogen-free)

Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V <sub>DS</sub>	100		V
Gate-Source Voltage		V <sub>GS</sub>	±		
Continuous Drain Current $(T_1 = 150 \text{ °C})^a$	T <sub>A</sub> = 25 °C	1	1.5	1.15	•
Continuous Drain Current $(T_J = 150^{\circ}C)^{\circ}$	T <sub>A</sub> = 70 °C	- I <sub>D</sub>	1.2	0.92	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	6		A
Avalanche Current <sup>b</sup>	L = 0.1 mH	I <sub>AS</sub>	6		
Single Avalanche Energy	L = 0.1 IIIH	E <sub>AS</sub>	1.8		mJ
Continuous Source Current (Diode Conduction) <sup>a</sup>		۱ <sub>S</sub>	0.6		А
Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25 °C	D	1.25	0.73	W
	T <sub>A</sub> = 70 °C	P <sub>D</sub>	0.80	0.47	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stq</sub>	- 55	to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	t ≤ 5 s	Р	80 100	100	
Maximum Sunction-to-Ambient	Steady State	R <sub>thJA</sub> 130 170	170	°C/W	
Maximum Junction-to-Foot	Steady State	R <sub>thJF</sub>	45	55	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

b. Pulse width limited by maximum junction temperature.

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<b>SPECIFICATIONS</b> (T <sub>A</sub> = 25	°C, unless	s otherwise noted)				
				Limits		
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 V, I_{D} = 1 mA$	100			V
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$	2		4	v
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA
Zara Cata Valtaga Drain Current	1	$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$	1		1	
Zero Gate Voltage Drain Current	IDSS	$V_{DS}$ = 100 V, $V_{GS}$ = 0 V, $T_{J}$ = 70 °C			75	μΑ
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 15 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	6			А
Drain-Source On-Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 1.5 A		0.195	0.250	Ω
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 1.5 A		4		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 1 A, V <sub>GS</sub> = 0 V		0.8	1.2	V
Dynamic <sup>b</sup>						
Total Gate Charge	Qg			3.3	5	
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ = 50 V, $V_{GS}$ = 10 V, $I_{D}$ = 1.5 A		0.47		nC
Gate-Drain Charge	Q <sub>gd</sub>			1.45		
Gate Resistance	Rg		0.5	1.3	2.4	Ω
Switching					•	
Turn-On Delay Time	t <sub>d(on)</sub>			7	11	
Rise Time	t <sub>r</sub>	$V_{DD}$ = 50 V, $R_L$ = 33 $\Omega$		11	17	1
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong 0.2$ Å, $V_{GEN} = 10$ V, $R_g = 6 \Omega$		9	15	ns
Fall Time	t <sub>f</sub>			10	15	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 1.5 A, dI/dt = 100 A/μs		50	100	

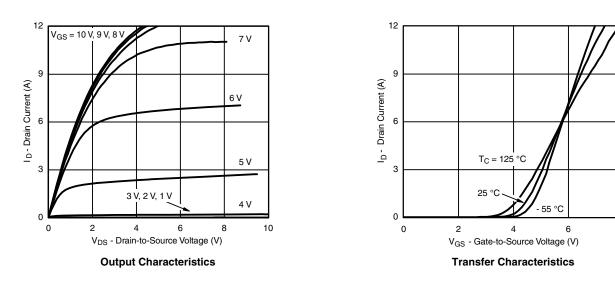
Notes:

a. Pulse test: PW  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



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# Si2328DS

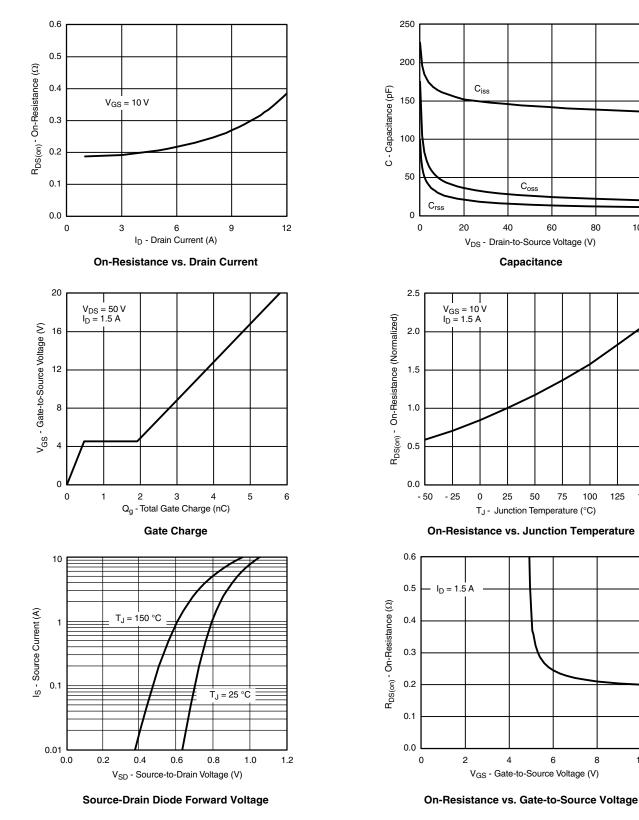
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Coss

Capacitance

T<sub>J</sub> - Junction Temperature (°C)

#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



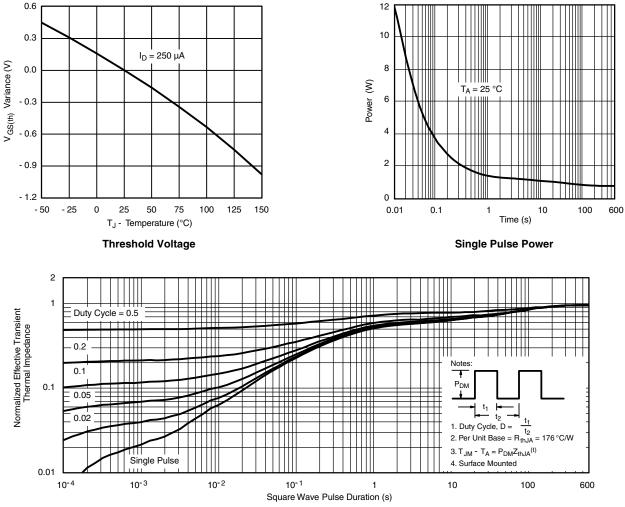
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## Si2328DS

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#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <u>www.vishay.com/ppg?71796</u>.

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## Package Information

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#### SOT-23 (TO-236): 3-LEAD







Dim	MILLIN	METERS	INCHES		
	Min	Max	Min	Мах	
Α	0.89	1.12	0.035	0.044	
A <sub>1</sub>	0.01	0.10	0.0004	0.004	
A <sub>2</sub>	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E <sub>1</sub>	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e <sub>1</sub>	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L <sub>1</sub>	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	



# Application Note 826

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#### **RECOMMENDED MINIMUM PADS FOR SOT-23**



Recommended Minimum Pads Dimensions in Inches/(mm)

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